Dieter H Bimberg

List of Publications by Year
in descending order

145 papers	4,612 citations	126907 33 h-index	118850 62 g-index
148 all docs	148 docs citations	148 times ranked	3061 citing authors

#	Article	IF	Citations
1	Spontaneous ordering of nanostructures on crystal surfaces. Reviews of Modern Physics, 1999, 71, 1125-1171.	45.6	925
2	Quantum dots: promises and accomplishments. Materials Today, 2011, 14, 388-397.	14.2	157
3	Vertical-cavity surface-emitting lasers for data communication and sensing. Photonics Research, 2019, 7, 121.	7.0	155
4	Quantum dots for lasers, amplifiers and computing. Journal Physics D: Applied Physics, 2005, 38, 2055-2058.	2.8	143
5	1550-nm High-Speed Short-Cavity VCSELs. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1158-1166.	2.9	124
6	Gain and Threshold of Quantum Dot Lasers: Theory and Comparison to Experiments. Japanese Journal of Applied Physics, 1997, 36, 4181-4187.	1.5	109
7	Metal-cavity surface-emitting microlaser at room temperature. Applied Physics Letters, 2010, 96, .	3.3	107
8	Theoretical and Experimental Study of High-Speed Small-Signal Cross-Gain Modulation of Quantum-Dot Semiconductor Optical Amplifiers. IEEE Journal of Quantum Electronics, 2009, 45, 240-248.	1.9	95
9	Few-particle energies versus geometry and composition of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> quantum dots. Physical Review B, 2009, 79, .	3.2	92
10	Quantum dots: lasers and amplifiers. Journal of Physics Condensed Matter, 2003, 15, R1063-R1076.	1.8	87
11	Ultrafast carrier dynamics in InGaAs quantum dot materials and devices. Journal of Optics, 2006, 8, S33-S46.	1.5	75
12	Static Gain Saturation Model of Quantum-Dot Semiconductor Optical Amplifiers. IEEE Journal of Quantum Electronics, 2008, 44, 658-666.	1.9	73
13	Strain effects and band parameters in MgO, ZnO, and CdO. Applied Physics Letters, 2012, 101, .	3.3	67
14	InGaAs/GaAs Quantum Dot Lasers with Ultrahigh Characteristic Temperature (T0=385K) Grown by Metal Organic Chemical Vapour Deposition. Japanese Journal of Applied Physics, 1997, 36, 4221-4223.	1.5	60
15	Energy Efficiency of Directly Modulated Oxide-Confined High Bit Rate 850-nm VCSELs for Optical Interconnects. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1702212-1702212.	2.9	57
16	20 Gb/s 85^{circ}C Error-Free Operation of VCSELs Based on Submonolayer Deposition of Quantum Dots. IEEE Journal of Selected Topics in Quantum Electronics, 2007, 13, 1302-1308.	2.9	56
17	High-Speed Mode-Locked Quantum-Dot Lasers and Optical Amplifiers. Proceedings of the IEEE, 2007, 95, 1767-1778.	21.3	53
18	Quantum Dots for Single- and Entangled-Photon Emitters. IEEE Photonics Journal, 2009, 1, 58-68.	2.0	52

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19	Theory of relaxation oscillations in semiconductor quantum dot lasers. Applied Physics Letters, 2006, 89, 101107.	3.3	50
20	Effect of Inhomogeneous Broadening on Gain and Phase Recovery of Quantum-Dot Semiconductor Optical Amplifiers. IEEE Journal of Quantum Electronics, 2010, 46, 1670-1680.	1.9	50
21	Progress in Quantum Dot Lasers: 1100 nm, 1300 nm, and High Power Applications. Japanese Journal of Applied Physics, 2000, 39, 2341-2343.	1.5	48
22	Theory of excitation transfer in coupled nanostructures â€" from quantum dots to light harvesting complexes. Physica Status Solidi (B): Basic Research, 2006, 243, 2302-2310.	1.5	48
23	Coulomb Damped Relaxation Oscillations in Semiconductor Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2007, 13, 1242-1248.	2.9	44
24	Static gain saturation in quantum dot semiconductor optical amplifiers. Optics Express, 2008, 16, 8269.	3.4	44
25	22-Gb/s Long Wavelength VCSELs. Optics Express, 2009, 17, 17547.	3.4	44
26	Impact of the Oxide-Aperture Diameter on the Energy Efficiency, Bandwidth, and Temperature Stability of 980-nm VCSELs. Journal of Lightwave Technology, 2015, 33, 825-831.	4.6	44
27	Progress in Epitaxial Growth and Performance of Quantum Dot and Quantum Wire Lasers. Journal of Lightwave Technology, 2008, 26, 1540-1555.	4.6	43
28	Error-Free Transmission Over 1-km OM4 Multimode Fiber at 25 Gb/s Using a Single Mode Photonic Crystal Vertical-Cavity Surface-Emitting Laser. IEEE Photonics Technology Letters, 2013, 25, 1823-1825.	2.5	40
29	Impact of Photon Lifetime on the Temperature Stability of 50 Gb/s 980 nm VCSELs. IEEE Photonics Technology Letters, 2016, 28, 2327-2330.	2.5	40
30	Large-Signal Response of Semiconductor Quantum-Dot Lasers. IEEE Journal of Quantum Electronics, 2010, 46, 1755-1762.	1.9	37
31	Progress on High-Speed 980â€‰nm VCSELs for Short-Reach Optical Interconnects. Advances in Optical Technologies, 2011, 2011, 1-15.	0.8	37
32	Quantum-Dot Semiconductor Mode-Locked Lasers and Amplifiers at 40 GHz. IEEE Journal of Quantum Electronics, 2009, 45, 1429-1435.	1.9	36
33	Energy-Efficient VCSELs for Interconnects. IEEE Photonics Journal, 2012, 4, 652-656.	2.0	36
34	Impact of the Quantum Well Gain-to-Cavity Etalon Wavelength Offset on the High Temperature Performance of High Bit Rate 980-nm VCSELs. IEEE Journal of Quantum Electronics, 2014, 50, 613-621.	1.9	36
35	80 Gb/s wavelength conversion using a quantum-dot semiconductor optical amplifier and optical filtering. Optics Express, 2011, 19, 5134.	3.4	32
36	Electro-optical resonance modulation of vertical-cavity surface-emitting lasers. Optics Express, 2012, 20, 5099.	3.4	32

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37	Two dimensional analysis of finite size high-contrast gratings for applications in VCSELs. Optics Express, 2014, 22, 11804.	3.4	32
38	Metal-cavity surface-emitting microlaser with hybrid metal-DBR reflectors. Optics Letters, 2011, 36, 2447.	3.3	30
39	Temperature-Dependent Small-Signal Analysis of High-Speed High-Temperature Stable 980-nm VCSELs. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 679-686.	2.9	29
40	Cross-Gain Modulation and Four-Wave Mixing for Wavelength Conversion in Undoped and p-Doped 1.3-<formula formulatype="inline"> <tex Notation="TeX">$muhbox{m}$</tex> </formula> Quantum Dot Semiconductor Optical Amplifiers. IEEE Photonics Journal, 2010, 2, 141-151.	2.0	29
41	40 Gb/s wavelength conversion via four-wave mixing in a quantum-dot semiconductor optical amplifier. Optics Express, 2011, 19, 3788.	3.4	29
42	InGaAs Quantum Dots Coupled to a Reservoir of Nonequilibrium Free Carriers. IEEE Journal of Quantum Electronics, 2009, 45, 1121-1128.	1.9	28
43	Numerical Simulation of Temporal and Spectral Variation of Gain and Phase Recovery in Quantum-Dot Semiconductor Optical Amplifiers. IEEE Journal of Quantum Electronics, 2010, 46, 405-413.	1.9	28
44	Atomic Structure of Buried InAs Sub-Monolayer Depositions in GaAs. Applied Physics Express, 2010, 3, 105602.	2.4	28
45	Confined States of Individual Type-II GaSb/GaAs Quantum Rings Studied by Cross-Sectional Scanning Tunneling Spectroscopy. Nano Letters, 2010, 10, 3972-3977.	9.1	28
46	Polarization switching and polarization mode hopping in quantum dot vertical-cavity surface-emitting lasers. Optics Express, 2011, 19, 2476.	3.4	28
47	High-Power Low-Beam Divergence Edge-Emitting Semiconductor Lasers with 1- and 2-D Photonic Bandgap Crystal Waveguide. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1113-1122.	2.9	27
48	Pulse Broadening in Quantum-Dot Mode-Locked Semiconductor Lasers: Simulation, Analysis, and Experiments. IEEE Journal of Quantum Electronics, 2011, 47, 935-943.	1.9	27
49	High-Speed Small-Signal Cross-Gain Modulation in Quantum-Dot Semiconductor Optical Amplifiers at 1.3 mum. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 749-756.	2.9	26
50	MOVPEâ€Growth of InGaSb/AlP/GaP(001) Quantum Dots for Nanoscale Memory Applications. Physica Status Solidi (B): Basic Research, 2018, 255, 1800182.	1.5	24
51	230â€‰s room-temperature storage time and 1.14â€‰eV hole localization energy in In0.5Ga0.5As quantum dots on a GaAs interlayer in GaP with an AlP barrier. Applied Physics Letters, 2015, 106, .	3.3	23
52	Multimode optical feedback dynamics in InAs/GaAs quantum dot lasers emitting exclusively on ground or excited states: transition from short- to long-delay regimes. Optics Express, 2018, 26, 1743.	3.4	23
53	Electronic states of (InGa)(AsSb)/GaAs/GaP quantum dots. Physical Review B, 2019, 100, .	3.2	23
54	Self-Organized InGaAs Quantum Dots for Advanced Applications in Optoelectronics. Japanese Journal of Applied Physics, 2002, 41, 949-952.	1.5	22

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55	Tilted Wave Lasers: A Way to High Brightness Sources of Light. IEEE Journal of Quantum Electronics, 2011, 47, 1014-1027.	1.9	22
56	Generation of ultra-wideband triplet pulses based on four-wave mixing and phase-to-intensity modulation conversion. Optics Express, 2012, 20, 20222.	3.4	22
57	Temperature-Dependent Characteristics of Single-Mode InAs Submonolayer Quantum-Dot Lasers. IEEE Photonics Technology Letters, 2012, 24, 906-908.	2.5	22
58	85-fJ Dissipated Energy Per Bit at 30 Gb/s Across 500-m Multimode Fiber Using 850-nm VCSELs. IEEE Photonics Technology Letters, 2013, 25, 1638-1641.	2.5	22
59	High-Brightness and Ultranarrow-Beam 850-nm GaAs/AlGaAs Photonic Band Crystal Lasers and Single-Mode Arrays. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 901-908.	2.9	21
60	Progress on single mode VCSELs for data- and tele-communications. Proceedings of SPIE, 2012, , .	0.8	21
61	InAs/GaAs Quantum Dots Grown by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1997, 36, 4129-4133.	1.5	20
62	Ultrafast VCSELs for Datacom. IEEE Photonics Journal, 2010, 2, 273-275.	2.0	20
63	Temperature-Stable 980-nm VCSELs for 35-Gb/s Operation at 85 Â°C With 139-fJ/bit Dissipated Heat. IEEE Photonics Technology Letters, 2014, 26, 2349-2352.	2.5	20
64	Large Bandwidth, Small Current Density, and Temperature Stable 980-nm VCSELs. IEEE Journal of Quantum Electronics, 2017, 53, 1-8.	1.9	20
65	VCSEL-Based Light Sourcesâ€"Scalability Challenges for VCSEL-Based Multi-100- Gb/s Systems. IEEE Photonics Journal, 2012, 4, 1831-1843.	2.0	19
66	Collective Light Emission Revisited: Reservoir Induced Coherence. Physical Review Letters, 2013, 110, 113604.	7.8	19
67	Theory and experiment of submonolayer quantum-dot metal-cavity surface-emitting microlasers. Optics Express, 2013, 21, 30336.	3.4	19
68	Temperature-Stable, Energy-Efficient, and High-Bit Rate Oxide-Confined 980-nm VCSELs for Optical Interconnects. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 405-413.	2.9	19
69	Optical response of (InGa)(AsSb)/GaAs quantum dots embedded in a GaP matrix. Physical Review B, 2019, 100, .	3.2	19
70	Uniform GaAs quantum wires formed on vicinal GaAs (110) surfaces by two-step MBE growth. Superlattices and Microstructures, 1997, 22, 43-49.	3.1	18
71	Polarization Switching in Quantum-Dot Vertical-Cavity Surface-Emitting Lasers. IEEE Photonics Technology Letters, 2009, 21, 1008-1010.	2.5	18
72	Strong amplitude-phase coupling in submonolayer quantum dots. Applied Physics Letters, 2016, 109, 201102.	3.3	18

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73	Comparison of optical feedback dynamics of InAs/GaAs quantum-dot lasers emitting solely on ground or excited states. Optics Letters, 2018, 43, 210.	3.3	18
74	Wide-Range Wavelength Conversion of 40-Gb/s NRZ-DPSK Signals Using a 1.3-mum Quantum-Dot Semiconductor Optical Amplifier. IEEE Photonics Technology Letters, 2012, 24, 1163-1165.	2.5	17
75	High-Speed and Temperature-Stable, Oxide-Confined 980-nm VCSELs for Optical Interconnects. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1701207-1701207.	2.9	17
76	Fast gain and phase recovery of semiconductor optical amplifiers based on submonolayer quantum dots. Applied Physics Letters, 2015, 107, .	3.3	17
77	Strain analysis from nano-beam electron diffraction: Influence of specimen tilt and beam convergence. Ultramicroscopy, 2018, 190, 45-57.	1.9	17
78	CW substrate-free metal-cavity surface microemitters at 300 K. Semiconductor Science and Technology, 2011, 26, 014012.	2.0	16
79	High Temperature Operation of 1060-nm High-Brightness Photonic Band Crystal Lasers With Very Low Astigmatism. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 722-727.	2.9	16
80	Spectral Efficiency and Energy Efficiency of Pulse-Amplitude Modulation Using 1.3 Î¼m Wafer-Fusion VCSELs for Optical Interconnects. ACS Photonics, 2017, 4, 2018-2024.	6.6	16
81	Post-growth p-type doping enhancement for ZnSe-based lasers using a Li3N interlayer. Applied Physics Letters, 2002, 81, 4916-4918.	3.3	15
82	Cavity-Volume Scaling Law of Quantum-Dot Metal-Cavity Surface-Emitting Microlasers. IEEE Photonics Journal, 2012, 4, 1103-1114.	2.0	15
83	Temperature-Dependent Impedance Characteristics of Temperature-Stable High-Speed 980-nm VCSELs. IEEE Photonics Technology Letters, 2015, 27, 832-835.	2.5	15
84	Astigmatism-free high-brightness 1060 nm edge-emitting lasers with narrow circular beam profile. Optics Express, 2016, 24, 30514.	3.4	15
85	1.55 µm high-speed VCSELs enabling error-free fiber-transmission up to 25 Gbit/s. , 2010, , .		14
86	Flying qubits and entangled photons. Laser and Photonics Reviews, 2014, 8, 276-290.	8.7	14
87	Thermal analysis of high-bandwidth and energy-efficient 980â€‰nm VCSELs with optimized quantum well gain peak-to-cavity resonance wavelength offset. Applied Physics Letters, 2017, 111, .	3.3	14
88	Semiconductor nanostructures for flying q-bits and green photonics. Nanophotonics, 2018, 7, 1245-1257.	6.0	14
89	Structural and compositional analysis of (InGa)(AsSb)/GaAs/GaP Stranskiâ€"Krastanov quantum dots. Light: Science and Applications, 2021, 10, 125.	16.6	14
90	Low Thermal Impedance of Substrate-Free Metal Cavity Surface-Emitting Microlasers. IEEE Photonics Technology Letters, 2011, 23, 1031-1033.	2.5	13

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91	Lateral-Longitudinal Modes of High-Power Inhomogeneous Waveguide Lasers. IEEE Journal of Quantum Electronics, 2012, 48, 123-128.	1.9	13
92	Spatial structure of In0.25Ga0.75As/GaAs/GaP quantum dots on the atomic scale. Applied Physics Letters, 2013, 102, .	3.3	13
93	Finite element simulation of the optical modes of semiconductor lasers. Physica Status Solidi (B): Basic Research, 2010, 247, 846-853.	1.5	12
94	Fabrication and room temperature operation of semiconductor nano-ring lasers using a general applicable membrane transfer method. Applied Physics Letters, 2017, 110, 171105.	3.3	12
95	Comparison between high- and zero-contrast gratings as VCSEL mirrors. Optics Communications, 2017, 389, 35-41.	2.1	12
96	Optimization of VCSEL photon lifetime for minimum energy consumption at varying bit rates. Optics Express, 2020, 28, 18931.	3.4	12
97	GaSb quantum dots on GaAs with high localization energy of 710 meV and an emission wavelength of 1.3 Âµm. Journal of Crystal Growth, 2014, 404, 48-53.	1.5	11
98	Hole localization energy of 1.18â€‰eV in GaSb quantum dots embedded in GaP. Physica Status Solidi (B): Basic Research, 2016, 253, 1877-1881.	1.5	10
99	On the importance of antimony for temporal evolution of emission from self-assembled (InGa)(AsSb)/GaAs quantum dots on GaP(001). New Journal of Physics, 2021, 23, 103029.	2.9	10
100	Demonstration of electrically injected vertical-cavity surface-emitting lasers with post-supported high-contrast gratings. Photonics Research, 2022, 10, 1170.	7.0	10
101	Disordering of CdZnSe/ZnSe Strained Layer Superlattices by Ion Implantation. Japanese Journal of Applied Physics, 1995, 34, 1159-1161.	1.5	9
102	Energy-Efficient 50+ Gb/s VCSELs for 200+ Gb/s Optical Interconnects. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-5.	2.9	9
103	Theory of Metal-Cavity Surface-Emitting Microlasers and Comparison With Experiment. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1681-1692.	2.9	8
104	Antimony-based quantum dot memories. Proceedings of SPIE, 2011, , .	0.8	8
105	Vertical-cavity surface-emitting lasers with nanostructures for optical interconnects. Frontiers of Optoelectronics, 2016, 9, 249-258.	3.7	8
106	Morphology and valence band offset of GaSb quantum dots grown on GaP(001) and their evolution upon capping. Nanotechnology, 2017, 28, 225601.	2.6	8
107	Quantum-Dot Semiconductor Optical Amplifiers for Energy-Efficient Optical Communication. Nanoscience and Technology, 2017, , 37-74.	1.5	8
108	Size-dependent luminescence of GaAs quantum wires on vicinal GaAs (110) surfaces with giant steps formed by MBE. Physica B: Condensed Matter, 1996, 227, 291-294.	2.7	7

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109	ZnMgCdSe structures on InP grown by MOVPE. Journal of Crystal Growth, 2000, 221, 416-420.	1.5	6
110	Direct Evidence of Nanoscale Carrier Localization in InGaN/GaN Structures Grown on Si Substrates. Japanese Journal of Applied Physics, 2003, 42, L1057-L1060.	1.5	6
111	Novel energy-efficient designs of vertical-cavity surface emitting lasers for the next generations of photonic systems. Japanese Journal of Applied Physics, 0, , .	1.5	6
112	GReen Data And Computer Communication. , 2011, , .		5
113	Leakage-Assisted Transverse Mode Selection in Vertical-Cavity Surface-Emitting Lasers With Thick Large-Diameter Oxide Apertures. IEEE Journal of Quantum Electronics, 2013, 49, 1034-1039.	1.9	5
114	Quantum-Dot Mode-Locked Lasers: Sources for Tunable Optical and Electrical Pulse Combs. Nanoscience and Technology, 2017, , 75-106.	1.5	5
115	Cathodoluminescence of strained quantum wells and layers. Superlattices and Microstructures, 1991, 9, 65-75.	3.1	4
116	Modeling Highly Efficient RCLED-Type Quantum-Dot-Based Single Photon Emitters. IEEE Journal of Quantum Electronics, 2009, 45, 1084-1088.	1.9	4
117	Room-Temperature Hysteresis in a Hole-Based Quantum Dot Memory Structure. Journal of Nanotechnology, 2013, 2013, 1-4.	3.4	4
118	Novel types of photonic band crystal high power and high brightness semiconductor lasers. Frontiers of Optoelectronics, 2016, 9, 225-237.	3.7	4
119	Formation of AlGaAs quantum wires on vicinal GaAs(110) surfaces misoriented 3Â° toward (111)A by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 35, 295-298.	3.5	3
120	Energy-efficient 1.3 μm short-cavity VCSELs for 30 Gb/s error-free optical links. , 2012, , .		3
121	Energy-efficient VCSELs for 200+ Gb/s optical interconnects. , 2019, , .		3
122	GaAs-based subwavelength grating on an AlOx layer for a vertical-cavity surface-emitting laser. OSA Continuum, 2020, 3, 317.	1.8	3
123	Effects of growth interruption on uniformity of GaAs quantum wires formed on vicinal GaAs(110) surfaces by MBE. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1998, 51, 229-232.	3.5	2
124	Onion-like growth of and inverted many-particle energies in quantum dots. Materials Science and Engineering C, 2005, 25, 698-704.	7.3	2
125	Single-Lobe Single-Wavelength Lasing in Ultrabroad-Area Vertical-Cavity Surface-Emitting Lasers Based on the Integrated Filter Concept. IEEE Journal of Quantum Electronics, 2008, 44, 724-731.	1.9	2
126	Linear and nonlinear semiconductor optical amplifiers. , 2010, , .		2

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127	Static and Dynamic Characteristics of In(AsSb)/ GaAs Submonolayer Lasers. IEEE Journal of Quantum Electronics, 2019, 55, 1-7.	1.9	2
128	910 nm Single-Mode VCSELs and its Application for Few-Mode Transmission over Graded-Index Single-Mode Fibers. , 2020, , .		2
129	Multi-aperture VCSELs: high power, low resistance, single mode. , 2021, , .		2
130	First observation of symmetry breaking in strained In0.7Ga0.3As/InP V-groove quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 969-973.	2.7	1
131	Dual Semiconductor Laser System With Rapid Time-Delay for Ultrafast Measurements. IEEE Photonics Technology Letters, 2006, 18, 2338-2340.	2.5	1
132	Quantum Dots: Genesis, the Excitonic Zoo, and its Applications. , 2007, , .		1
133	Nanophotonics for a green internet. , 2019, , .		1
134	Novel VCSEL Designs for the next generation of photonic systems. , 2021, , .		1
135	High-power, single-mode, multi-aperture VCSELs for long-reach optical interconnects. , 2021, , .		1
136	Collaborative Research Programs in Germany and the EU. , 2007, , .		0
137	Epitaxy of multimodal InAs/GaAs quantum dot ensembles. Journal of Crystal Growth, 2007, 298, 567-569.	1.5	0
138	Magnetooptical properties of quantum dots: Influence of the piezoelectric field. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1163-1165.	2.7	0
139	Correction to â€œEnergy Efficiency of Directly Modulated Oxide-confined High Bit Rate 850Ânm VCSELs for Optical Interconnectsâ€•[Jul/Aug 13 1702212]. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 335-335.	2.9	0
140	Nanophotonics for future data communication and ethernet networks. , 2015, , .		0
141	High-contrast-grating-based Fabry-PÃ©rot filter array for monolithic multiwavelength VCSEL arrays. , 2016, , .		0
142	1060-nm High Brightness Picosecond Pulse Generation in Photonic Band Crystal Lasers. IEEE Photonics Technology Letters, 2016, 28, 2086-2089.	2.5	0
143	How can we accommodate the rapidly increasing power consumption of the internet? â€œGreenâ€•optical interconnects based on novel VCSELs. , 2017, , .		0
144	Cathodoluminescence observation of GaAs-AlGas heterointerfaces.. Hyomen Kagaku, 1989, 10, 697-702.	0.0	0

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145	High-power, low resistance, single-mode, multi-aperture VCSELs. , 2021, , .		0